

RAYCONN ELECTRONICS CO., LTD.

SPECIFICATION FORM

FEATURES

- ✧ 0.56 INCHES (14.20MM) DIGIT HEIGHT
- ✧ 50.30MM×19.0MM OUTLINE
- ✧ FOUR DIGIT
- ✧ SINGLE COLOR
- ✧ EASY ASSEMBLY
- ✧ HIGH BRIGHTNESS
- ✧ SOLID STATE RELIABILITY

DESCRIPTION

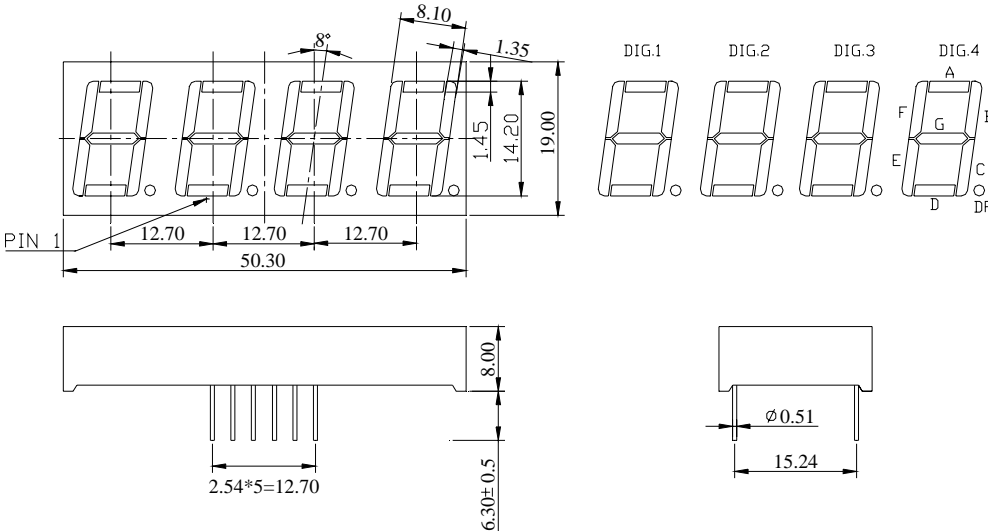
The REC-S5461ASR is a 0.56 inches(14.20mm) digit height, 50.30mm×19.0mm outline, single color, four digit and common anode numeric display. This display utilizes super-red LED chips fabricated from GaAlAs epiwafer on GaAs substrate grown by liquid phase epitaxy. These devices have black face and white segments.

DEVICE

PART NO.	EMITTING COLOR	DESCRIPTION
REC-S5461ASR	Super-Red	Black Face & White Segments

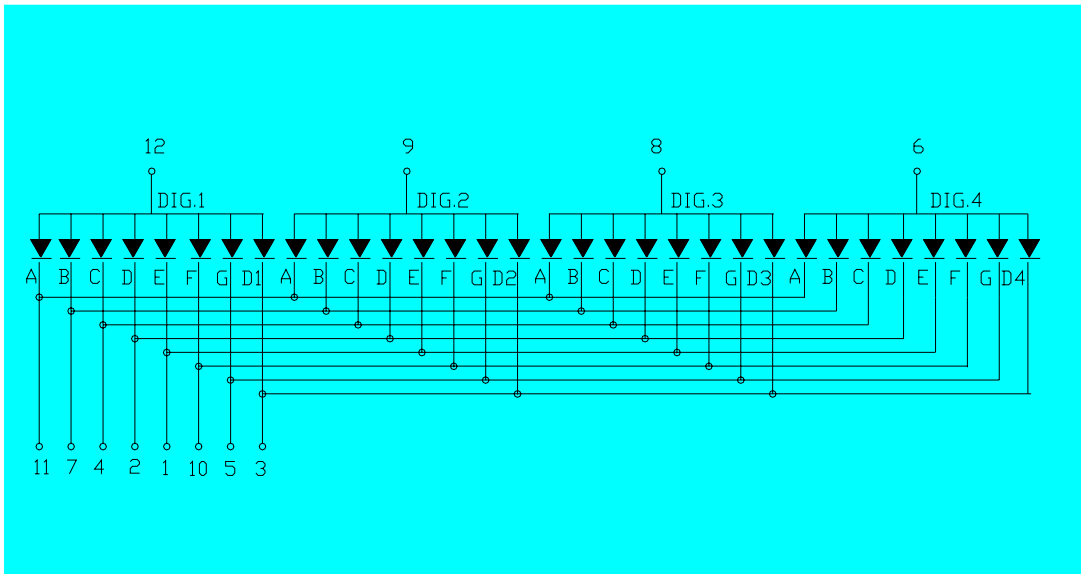
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PACKAGE DIMENSION



Note: Tolerance is $\pm 0.25\text{mm}$ unless otherwise noted.

INTERNAL CIRCUIT DIAGRAM



PIN CONNECTION

PIN NO.	CONNECTION	PIN NO.	CONNECTION
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1	Cathode E	7	Cathode B
2	Cathode D	8	Common Anode Dig.3
3	Cathode DP	9	Common Anode Dig.2
4	Cathode C	10	Cathode F
5	Cathode G	11	Cathode A
6	Common Anode Dig.4	12	Common Anode Dig.1

ABSOLUTE MAXIMUM RATING AT $T_A=25^\circ\text{C}$

PARAMETER	SYMBOL	MAXIMUM	UNIT
Power Dissipation per Seg.	P_{AD}	60	mW
Peak Forward Current per Seg.	I_{PF}	80	mA
Continuous Forward Current per Seg.	I_{AF}	20	mA
Reverse Voltage per Seg.	V_R	5	V
Operating Temperature Range, T_{opr}	- 25° C to + 60° C		
Storage Temperature Range, T_{stg}	- 30° C to + 85° C		
Solder Temperature : 1 / 16 inch below seating plane for 3 seconds at 260° C			

ELECTRO – OPTICAL CHARACTERISTICS AT $T_A=25^\circ\text{C}$

PARAMETER	UNIT	MIN	TYPE	MAX
Luminous Intensity per Seg., I_V ($I_F=20\text{mA}$)	mcd	7	10	14
Peak Emission Wavelength, λ_P ($I_F=20\text{mA}$)	nm		640	
Special Line Half-Width, $\Delta\lambda$ ($I_F=20\text{mA}$)	nm		20	
Forward Voltage per Seg., V_F ($I_F=20\text{mA}$)	V	1.6	1.8	2.1
Reverse Current per chipSeg., I_R , ($V_R=5\text{V}$)	μA			100